

AMENDMENTS TO THE CLAIMS:

Please cancel claims 21-31, without prejudice, and amend claims 1, 4 and 18, as shown below.

This listing of claims will replace all prior versions and listings of claims in the Application:

Claim 1 (currently amended): A semiconductor device manufacturing apparatus that uses a thermal CVD reaction to deposit a film onto a substrate, said apparatus having a vaporizer for vaporizing a raw material to form a vapor phase deposition material and an orienting element using a d.c. electrical potential for orienting precursor molecules on a surface of said substrate or the deposited film in the direction of the electrical field induced by said d.c. electrical potential.

Claim 2 (previously presented): A semiconductor device manufacturing apparatus according to claim 1, wherein said orienting element comprises a power supply for supplying said d.c. electrical potential to said substrate or said film deposited thereupon, either directly or indirectly.

Claim 3 (previously presented): A semiconductor device manufacturing apparatus according to claim 2, wherein said power supply comprises a power supply source and electrode terminals which are connected to said power supply source and to said substrate or said film deposited thereupon.

Claim 4 (currently amended): A semiconductor device manufacturing apparatus ~~according to claim 2,~~ that uses a thermal CVD reaction to deposit a film onto a substrate, said apparatus having a vaporizer for vaporizing a raw material to form a vapor phase deposition material and an orienting element using a d.c. electrical potential for orienting precursor

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE
SUITE 140
TUCSON, AZ 85718
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

molecules in the direction of the electrical field induced by said d.c. electrical potential,
wherein said orienting element comprises a power supply which comprises a power supply
source and electrode terminals which are connected to said power supply source and to said
substrate or said film deposited thereupon for supplying said d.c. electrical potential to said
substrate or said film deposited thereupon, either directly or indirectly, and wherein said power supply further comprises a d.c. electrical potential controller which controls said potential to be supplied to said substrate or said film deposited thereupon.

Claim 5 (previously presented): A semiconductor device manufacturing apparatus according to claim 4, wherein said d.c. electrical potential controller controls said potential to be supplied to said substrate or said film deposited thereupon, either continuously or intermittently.

Claim 6 (previously presented): A semiconductor device manufacturing apparatus according to claim 4, wherein at least one electrode terminal is provided on a peripheral area of either said substrate or a region on which said film is deposited on said substrate.

Claims 7-10 (cancelled)

Claim 11 (previously presented): A semiconductor device manufacturing apparatus according to claim 4, wherein said d.c. electrical potential controller controls said voltage applied to at least one of a pair of electrode terminal units so as to change said voltage value, either continuously or intermittently with respect to the time elapsing.

Claim 12 (cancelled)

Claim 13 (previously presented): A semiconductor device manufacturing apparatus according to claim 4, wherein said d.c. electrical potential controller further includes a detector for detecting either one of potential and voltage applied to said substrate or said film deposited

thereupon whereby said d.c. electrical potential controller controls the value of either said potential or said voltage in response to a result of said detector.

Claim 14 (previously presented): A semiconductor device manufacturing apparatus according to claim 4, said apparatus further provided with a temperature controller for controlling the temperature of electrode terminal units and wherein said d.c. electrical potential controller further includes a detector for detecting either one of potential or voltage applied to said substrate or said film deposited thereupon whereby said temperature controller controls temperature so as to change a temperature of said substrate or said film deposited thereupon, in response to a result of said detector.

Claims 15-17 (cancelled)

Claim 18 (currently amended): A semiconductor device manufacturing apparatus according to claim 2, that uses a thermal CVD reaction to deposit a film onto a substrate, said apparatus having a vaporizer for vaporizing a raw material to form a vapor phase deposition material and an orienting element using a d.c. electrical potential for orienting precursor molecules in the direction of the electrical field induced by said d.c. electrical potential, wherein said orienting element comprises a power supply for supplying said d.c. electrical potential to said substrate or said film deposited thereupon, either directly or indirectly, and wherein said power supply comprises a power supply source and a non-contact electrical potential supply which is connected to said power supply source and supplying said d.c. electrical potential to said substrate or said film deposited thereupon, without making said potential supply be directly connected thereto.

Claim 19 (cancelled)

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE
SUITE 140
TUCSON, AZ 85718
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

Claim 20 (previously presented): A semiconductor device manufacturing apparatus according to claim 18, wherein said power supply further comprises a potential controller which controls value of said potential to be applied to said non-contact electrical potential supply.

Claims 21-31 (cancelled)

Claim 32 (cancelled)

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE
SUITE 140
TUCSON, AZ 85718
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567